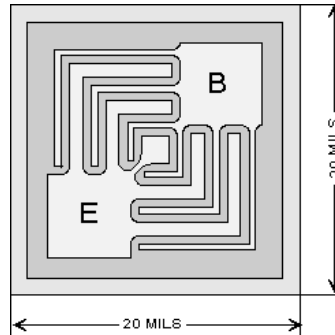


**Chip Type 2C2904A**  
**Geometry 0600**  
**Polarity PNP**

**Generic Packaged Parts:**  
**2N2904A**



[Request Quotation](#)

Chip type **2C2904A** by Semicoa Semiconductors provides performance similar to these devices.

**Product Summary:**

**APPLICATIONS:** Designed for general purpose switching and amplifier applications.

**Part Numbers:**

2N2904A, 2N2904, 2N2906A, 2N2906,  
 2N2904AUB, SD2904A, SD2904AF, SQ2904A,  
 SQ2904AF, 2N3485, 2N3485A

**Features:**

Mechanical Specifications		
Metallization	Top	Al - 18 kÅ min.
	Backside	Au - 6.5 kÅ nom.
Bonding Pad Size	Emitter	4.0 mils x 4.0 mils
	Base	4.0 mils x 4.0 mils
Die Thickness	8 mils nominal	
Chip Area	20 mils x 20 mils	
Top Surface	Silox Passivated	

Electrical Characteristics				
$T_A = 25^\circ\text{C}$				
Parameter	Test conditions	Min	Max	Unit
$BV_{CEO}$	$I_C = 10.0 \text{ mA}, I_B = 0$	60	---	V dc
$BV_{CBO}$	$I_C = 10 \mu\text{A}, I_E = 0$	60	---	V dc
$BV_{EBO}$	$I_E = 10 \mu\text{A}, I_C = 0$	5.0	---	V dc
$I_{CBO}$	$V_{CB} = 50 \text{ V}, I_E = 0$	---	10	nA
$h_{FE}$	$I_C = 150 \text{ mA dc}, V_{CE} = 10 \text{ V}$	40	120	---

*Due to limitations of probe testing, only dc parameters are tested. This must be done with pulse width less than 300  $\mu\text{s}$ , duty cycle less than 2%.*